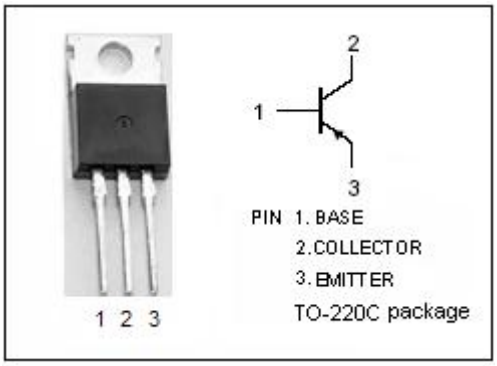
isc Silicon PNP Power Transistor — 2SA1069

DESCRIPTION

- Low Collector Saturation Voltage
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

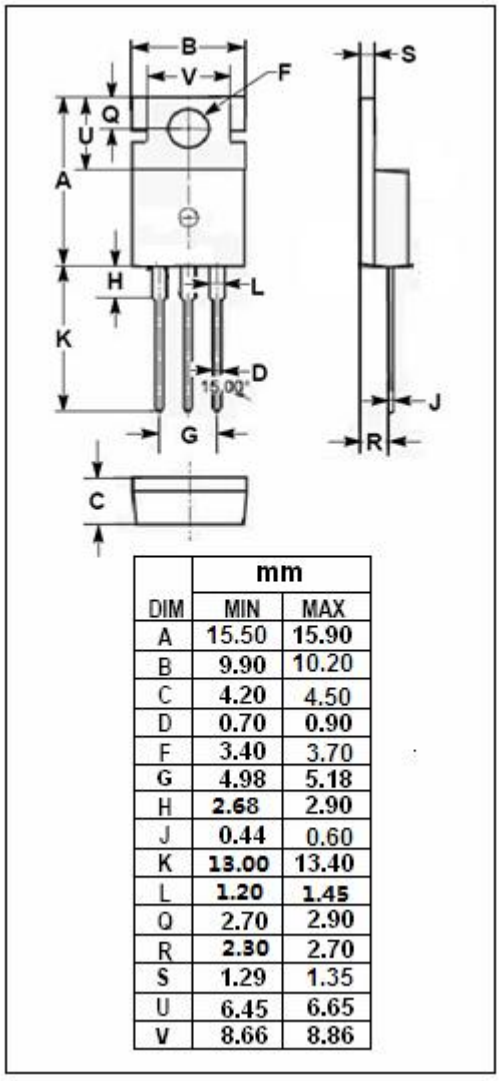


APPLICATIONS

- Designed for high-speed switching, and is ideal for use as a driver in devices such as switching reglators,DC/DC converters, and high frequency power amplifiers.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-12	V
I_C	Collector Current-Continuous	-5	A
I_{CM}	Collector Current-Peak	-10	A
I_B	Base Current-Continuous	-2.5	A
P_C	Collector Power Dissipation @ T_a=25℃	1.5	W
	Total Power Dissipation @ T_C=25℃	30	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.90	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	13.00	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

isc Silicon PNP Power Transistor 2SA1069

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -3.0A ; I_B= -0.3A, L=1mH	-60		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -3.0A; I_B= -0.3A		-0.6	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -3.0A; I_B= -0.3A		-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -60V; I_E= 0		-10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C=0		-10	μA
h_{FE-1}	DC Current Gain	I_C= -0.3A; V_{CE}= -5V	40		
h_{FE-2}	DC Current Gain	I_C= -3.0A; V_{CE}= -5V	40	200	

◆ **h_{FE-2} Classifications**

M	L	K
40-80	60-120	100-200